I 1 cancel'd example, 500Å. Further, the semiconductor layer is covered by an insulating layer 59 made of silicon oxide or silicon nitride and having a thickness of 200-1500Å.

IN THE CLAIMS:

Please cancel claims 14 and 16 without prejudice or disclaimer of the subject matter contained therein.

Please amend claims 1, 6, and 11 as follows. The amendments to the claims are outlined in the Attachment to the Amendment using the conventional method of bracketing and underlining.

I 2

1. (Three Times Amended) A laser irradiation method comprising:

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction; and

condensing said masked laser beam in a second direction orthogonal to said first direction after removing said portion to form a condensed laser beam, said condensed laser beam having a third cross section;

scanning an object with the condensed laser beam in a direction orthogonal to the first direction,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction.

I 3

6. (Twice Amended) A laser irradiation method comprising:

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction; and

condensing said masked laser beam in a second direction orthogonal to said first direction after removing said portion to form a condensed laser beam, said condensed laser beam having a third cross section;

I3 amd'd

scanning an object with the condensed laser beam in a direction orthogonal to the first direction,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction, and

wherein the length of the third cross section in the first direction is longer than a length of the first cross section in the first direction, and the width of the third cross section in the second direction is smaller than the width of the first cross section in the second direction.

I4

11. (Three Times Amended) A method comprising:

forming a semiconductor film over a substrate;

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction;

condensing said masked laser beam in a second direction orthogonal to said first direction to form a condensed laser beam after removing said portion, said condensed laser beam having a third cross section;

irradiating said semiconductor film with the condensed laser beam to crystallize said semiconductor film; and

scanning the semiconductor film with the condensed laser beam in a direction orthogonal to the first direction,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction.

Please add new claims 110-123 as follows:

110. (New) The method according to claim 1 wherein each of said first, second and third cross sections has a rectangular shape.

J5

111. (New) The method according to claim 6 wherein each of said first, second and third cross sections has a rectangular shape.

112. (New) The method according to claim 11 wherein each of said first, second and third cross sections.

113. (New) A method comprising:

forming a semiconductor film over a substrate;

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction;

condensing said masked laser beam in a second direction orthogonal to said first direction to form a condensed laser beam after removing said portion, said condensed laser beam having a third cross section;

irradiating said semiconductor film with the condensed laser beam to crystallize said semiconductor film; and

scanning the semiconductor film with respect to the condensed laser beam in a direction orthogonal to the first direction,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction, and

wherein the length of the third cross section in the first direction is longer than a length of the first cross section in the first direction, and the width of the third cross

section in the second direction is smaller than the width of the first cross section in the second direction.

114. (New) A method comprising:

forming a semiconductor film over a substrate;

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam to form an expanded laser beam;

removing a portion of the expanded laser beam through a mask to form a masked laser beam;

condensing said masked laser beam to form a condensed laser beam after removing said portion; and

irradiating said semiconductor film with the condensed laser beam to crystallize said semiconductor film.

115. (New) The method according to claim 114 wherein said laser beam is a pulsed laser beam.

116. (New) The method according to claim 114 wherein said laser beam is a pulsed excimer laser beam.

117. (New) The method according to claim 114 wherein said semiconductor film is formed over an ion blocking film formed on said substrate.

118. (New) A method comprising:

forming a semiconductor film over a substrate;

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction;

condensing said masked laser beam in a second direction orthogonal to said first direction to form a condensed laser beam after removing said portion, said condensed laser beam having a third cross section; and

irradiating said semiconductor film with the condensed laser beam to crystallize said semiconductor film,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction.

119. (New) The method according to claim 118 wherein said laser beam is a pulsed laser beam.

I 5 cont'd

120. (New) The method according to claim 118 wherein said laser beam is a pulsed excimer laser beam.

121. (New) The method according to claim 118 wherein the length of the third cross section in the first cross section is longer than a length of the first cross section in the first direction, and the width of the third cross section in the second direction is smaller than the width of the first direction in the second direction.

122. (New) The method according to claim 118 wherein each of said first, second and third cross sections.

123. (New) The method according to claim 118 wherein said semiconductor film is formed over an ion blocking film formed on said substrate.

124. (New) The method according to claim 113 wherein each of said first, second and third cross sections has a rectangular shape.

125. (New) The method according to claim 11 wherein said semiconductor film comprises amorphous silicon and a thickness of said semiconductor film is 200 to 1500 Å.

126. (New) The method according to claim 113 wherein said semiconductor film comprises amorphous silicon and a thickness of said semiconductor film is 200 to 1500 Å.

127. (New) The method according to claim 114 wherein said semiconductor film comprises amorphous silicon and a thickness of said semiconductor film is 200 to 1500 Å.

128. (New) The method according to claim 118 wherein said semiconductor film comprises amorphous silicon and a thickness of said semiconductor film is 200 to 1500 Å.

129. (New) The method according to claim 17 wherein said laser beam is a pulsed laser beam and said substrate is moved in a stepwise manner.

I 5 cont'd

130. (New) The method according to claim 17 wherein said laser beam is a pulsed laser beam and said substrate is moved while one site of said film is irradiated with the condensed laser beam at a plurality of times.

131. (New) The method according to claim 61 wherein said laser beam is a pulsed laser beam and said substrate is moved in a stepwise manner.

132. (New) The method according to claim 1 wherein said laser beam is a pulsed laser beam and said object is moved with respect to the condensed laser beam in a stepwise manner.

133. (New) The method according to claim 6 wherein said laser beam is a pulsed laser beam and said object is moved.

134. (New) The method according to claim 1 wherein said laser beam is a pulsed laser beam and said object is moved while one side of said object is irradiated with the condensed laser beam at a plurality of times.

135. (New) The method according to claim 6 wherein said laser beam is a pulsed laser beam and said object is moved while one site of said object is irradiated with the condensed laser